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(71) Applicant *(for all designated States except US)*: **MICRON TECHNOLOGY, INC.** [US/US]; 8000 South Federal Way, Boise, Idaho 83716-9632 (US).

(72) Inventors; and

(75) Inventors/Applicants *(for US only)*: **YIN, Zhiping** [US/US]; 1462 East Regatta Street, Boise, Idaho 83706 (US). **LI, Weimin** [CN/CN]; 18 Qington Road #43-502, Pudong New Area, Shanghai 201203 (CN).

(74) Agents: **STEFFEY, Charles, E.** et al.; P.O. Box 2938, Minneapolis, Minnesota 55402 (US).

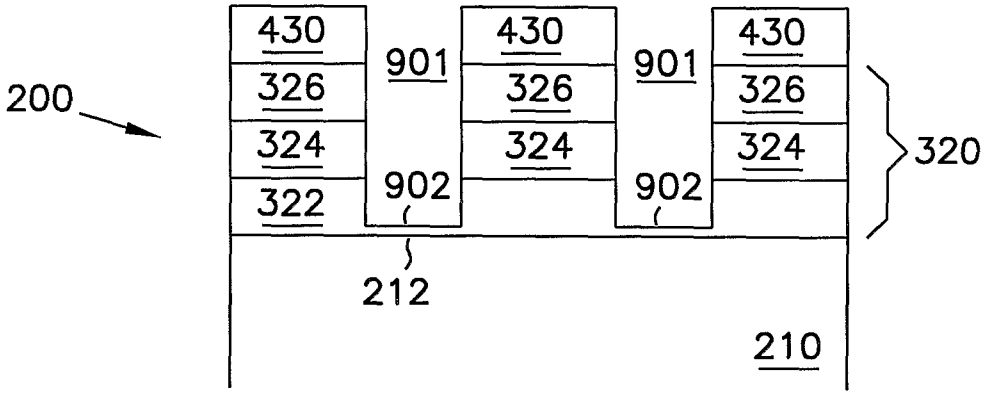
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(54) Title: TRANSPARENT AMORPHOUS CARBON STRUCTURE IN SEMICONDUCTOR DEVICES



(57) Abstract: A transparent amorphous carbon layer is formed. The transparent amorphous carbon layer has a low absorption coefficient such that the amorphous carbon is transparent in visible light. The transparent amorphous carbon layer may be used in semiconductor devices for different purposes. The transparent amorphous carbon layer may be included in a final structure in semiconductor devices. The transparent amorphous carbon layer may also be used as a mask in an etching process during fabrication of semiconductor devices.

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